Octal 3-State Noninverting D Flip-Flop with LSTTL-Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT574A is identical in pinout to the LS574. This device may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

Data meeting the setup time is clocked to the outputs with the rising edge of the Clock. The Output Enable input does not affect the states of the flip-flops, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be stored even when the outputs are not enabled.

The HCT574A is identical in function to the HCT374A but has the flip—flop inputs on the opposite side of the package from the outputs to facilitate PC board layout.

Features

- Output Drive Capability: 15 LSTTL Loads
- TTL NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 286 FETs or 71.5 Equivalent Gates
- Pb-Free Packages are Available*



ON Semiconductor®

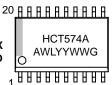
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MARKING DIAGRAMS



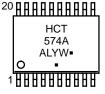
PDIP-20 N SUFFIX CASE 738 

SOIC-20 DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Package
 Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

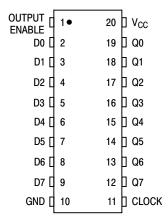


Figure 1. Pin Assignment

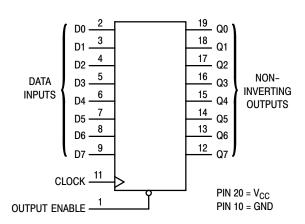


Figure 2. Logic Diagram

| Design Criteria | Value | Units |
|---------------------------------|--------|-------|
| Internal Gate Count* | 71.5 | ea |
| Internal Gate Propagation Delay | 1.5 | ns |
| Internal Gate Power Dissipation | 5.0 | μW |
| Speed Power Product | 0.0075 | рЈ |

^{*}Equivalent to a two-input NAND gate.

FUNCTION TABLE

| | | Output | | |
|---|----|---------|---|-----------|
| | OE | Clock | D | Q |
| ĺ | L | 7 | Н | Н |
| ı | L | | L | L |
| ı | L | L,H, ∕_ | X | No Change |
| ١ | Н | Х | Х | Z |

X = don't careZ = high impedance

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|------------------|---------------------------|-----------------------|
| MC74HCT574AN | PDIP-20 | 18 Units / Box |
| MC74HCT574ANG | PDIP-20 (Pb-Free) | 18 Units / Box |
| MC74HCT574ADW | SOIC-20 WIDE | 38 Units / Rail |
| MC74HCT574ADWG | SOIC-20 WIDE (Pb-Free) | 38 Units / Rail |
| MC74HCT574ADWR2 | SOIC-20 WIDE | 1000 Tape & Reel |
| MC74HCT574ADWR2G | SOIC-20 WIDE (Pb-Free) | 1000 Tape & Reel |
| MC74HCT574ADTR2 | TSSOP-20* | 2500 Tape & Reel |
| MC74HCT574ADTR2G | TSSOP-20* | 2500 Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|------------------|-------------------------------------------------------------------------------|--------------------------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | - 0.5 to + 7.0 | V |
| V _{in} | DC Input Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| V _{out} | DC Output Voltage (Referenced to GND) | -0.5 to $V_{CC} + 0.5$ | V |
| I _{in} | DC Input Current, per Pin | ± 20 | mA |
| I _{out} | DC Output Current, per Pin | ± 35 | mA |
| I _{CC} | DC Supply Current, V _{CC} and GND Pins | ± 75 | mA |
| P _D | Power Dissipation in Still Air, Plastic DIP† SOIC Package† | 750 500 | mW |
| T _{stg} | Storage Temperature | - 65 to + 150 | °C |
| TL | Lead Temperature, 1 mm from Case for 10 secs (Plastic DIP or SOIC Package) | 260 | °C |

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating – Plastic DIP: –10 mW/°C from 65° to 125°C – SOIC Package: –7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|------------------------------------|------------------------------------------------------|------|-------|------|
| V _{CC} | DC Supply Voltage (Referenced to GND) | 4.5 | 5.5 | V |
| V _{in} , V _{out} | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | Vcc | V |
| T _A | Operating Temperature, All Package Types | - 55 | + 125 | °C |
| t _r , t _f | Input Rise and Fall Time (Figure 3) | | 500 | ns |

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| | | | | Gu | Guaranteed Limit | | |
|-----------------|------------------------------------------------|--------------------------------------------------------------------------------------------------|-----------------|------------------|------------------|------------|------|
| Symbol | Parameter | Test Conditions | V _{CC} | – 55 to 25°C | ≤ 85°C | ≤ 125°C | Unit |
| V _{IH} | Minimum High-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 4.5 5.5 | 2.0 2.0 | 2.0 2.0 | 2.0 2.0 | V |
| V _{IL} | Maximum Low-Level Input Voltage | $V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$ | 4.5 5.5 | 0.8 0.8 | 0.8 0.8 | 0.8 0.8 | V |
| V _{OH} | Minimum High-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$ | 4.5 5.5 | 4.4 5.4 | 4.4 5.4 | 4.4 5.4 | |
| | | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ | 4.5 | 3.98 | 3.84 | 3.7 | V |
| V _{OL} | Maximum Low-Level Output Voltage | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$ | 4.5 5.5 | 0.1 0.1 | 0.1 0.1 | 0.1 0.1 | |
| | | $V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ | 4.5 | 0.26 | 0.33 | 0.4 | |
| I _{in} | Maximum Input Leakage Current | V _{in} = V _{CC} or GND | 5.5 | ± 0.1 | ± 1.0 | ± 1.0 | μΑ |
| I _{CC} | Maximum Quiescent Supply Current (per Package) | $V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$ | 5.5 | 4.0 | 40 | 160 | μΑ |
| l _{OZ} | Maximum Three–State Leakage Current | $V_{in} = V_{IL} \text{ or } V_{IH} \text{ (Note 1)}$ $V_{out} = V_{CC} \text{ or GND}$ | 5.5 | - 0.5 | - 5.0 | - 10 | μΑ |
| ΔI_{CC} | Additional Quiescent Supply Current | V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs | | ≥ - 55 °C | 25°C to | 125°C | |
| | | $I_{\text{out}} = 0 \mu\text{A}$ | 5.5 | 2.9 | 2 | .4 | mA |

1. Output in high-impedance state.

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = $5.0 \text{ V} \pm 10\%$, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

| | | Guaranteed Limit | | | |
|----------------------------------------|----------------------------------------------------------------------|------------------|----------------|---------|------|
| Symbol | Parameter | – 55 to 25°C | ≤ 85 °C | ≤ 125°C | Unit |
| f _{MAX} | Maximum Clock Frequency (50% Duty Cycle) (Figures 3 and 6) | 30 | 24 | 20 | MHz |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Clock to Q (Figures 3 and 6) | 30 | 38 | 45 | ns |
| t _{PLZ} , t _{PHZ} | Maximum Propagation Delay, Output Enable to Q (Figures 4 and 7) | 28 | 35 | 42 | ns |
| t _{PZH} , t _{PZL} | Maximum Propagation Delay Time, Output Enable to Q (Figures 4 and 7) | 28 | 35 | 42 | ns |
| t _{TLH} , | Maximum Output Transition Time, Any Output (Figures 3, 4 and 6) | 12 | 15 | 18 | ns |
| t _{THL} | | | | | |
| C _{in} | Maximum Input Capacitance | 10 | 10 | 10 | pF |

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

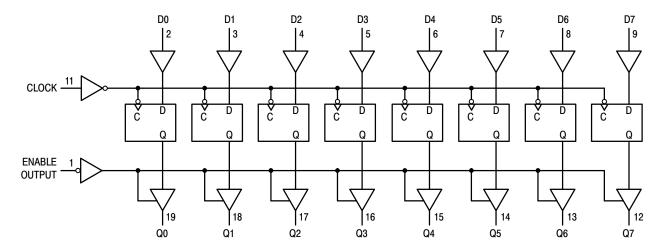
| | | Typical @ 25°C, V _{CC} = 5.0 V | |
|----------|------------------------------------------------|-----------------------------------------|----|
| C_{PD} | Power Dissipation Capacitance (Per Flip-Flop)* | 58 | pF |

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

| | | | Guaranteed Limit | | | | | | |
|---------------------|-----------------------------------|--------|------------------|------|------|-----|------|------|------|
| | | | – 55 to | 25°C | ≤ 8 | 5°C | ≤ 12 | 25°C | |
| Symbol | Parameter | Figure | Min | Max | Min | Max | Min | Max | Unit |
| t _{su} | Minimum Setup Time, Data to Clock | 5 | 10 | | 13 | | 15 | | ns |
| t _h | Minimum Hold Time, Clock to Data | _ 5 _ | _5.0 _ | | _5.0 | _ | 5.0 | | ns |
| t _w | Minimum Pulse Width, Clock | 3 | 15 | | 19 | | 22 | | ns |
| t _r , If | Maximum Input Rise and Fall Times | 3 | | 500 | | 500 | | 500 | ns |

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

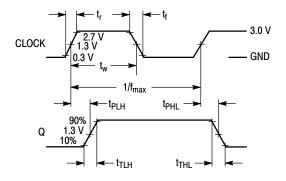


Figure 3.

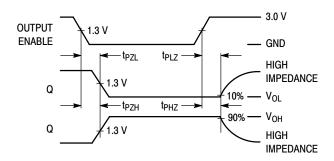


Figure 4.

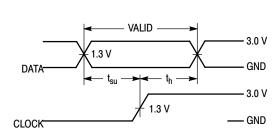
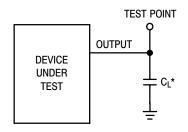


Figure 5.



*Includes all probe and jig capacitance

Figure 6. Test Circuit

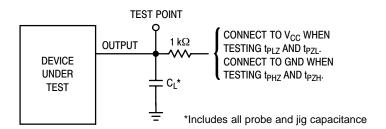
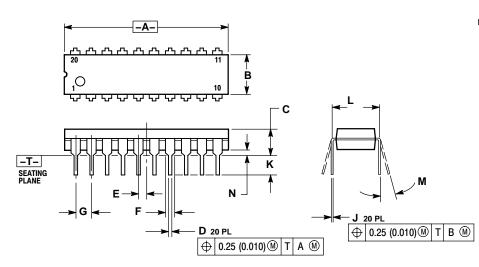


Figure 7. Test Circuit

PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEAD WHEN
- FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

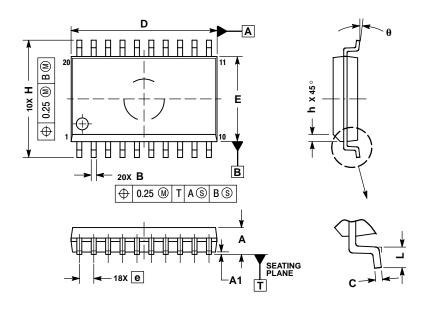
| | INCHES | | MILLIN | IETERS |
|-----|-----------|-------|----------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 1.010 | 1.070 | 25.66 | 27.17 |
| В | 0.240 | 0.260 | 6.10 | 6.60 |
| С | 0.150 | 0.180 | 3.81 | 4.57 |
| D | 0.015 | 0.022 | 0.39 | 0.55 |
| Е | 0.050 BSC | | 1.27 | BSC |
| F | 0.050 | 0.070 | 1.27 | 1.77 |
| G | 0.100 | BSC | 2.54 BSC | |
| J | 0.008 | 0.015 | 0.21 | 0.38 |
| K | 0.110 | 0.140 | 2.80 | 3.55 |

0.300 BSC

N 0.020 0.040

7.62 BSC

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G**



NOTES:

- NOTES:

 1. DIMENSIONS ARE IN MILLIMETERS.

 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

 3. DIMENSIONS O AND E DO NOT INCLUDE MOLD

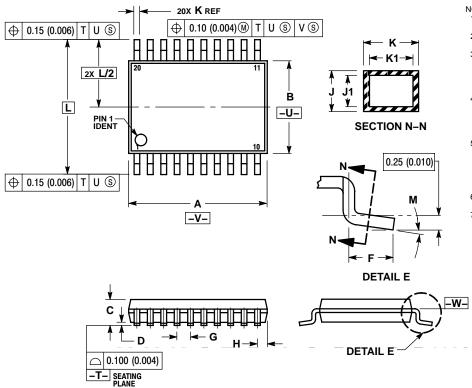
DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | | | |
|-----|-------------|-------|--|--|--|
| DIN | MIN | MAX | | | |
| Α | 2.35 | 2.65 | | | |
| A1 | 0.10 | 0.25 | | | |
| В | 0.35 | 0.49 | | | |
| С | 0.23 | 0.32 | | | |
| D | 12.65 | 12.95 | | | |
| E | 7.40 | 7.60 | | | |
| е | 1.27 | BSC | | | |
| Н | 10.05 | 10.55 | | | |
| h | 0.25 | 0.75 | | | |
| L | 0.50 | 0.90 | | | |
| θ | 0 ° | 7 ° | | | |

PACKAGE DIMENSIONS

TSSOP-20 DT SUFFIX 20 PIN PLASTIC TSSOP PACKAGE CASE 948E-02

ISSUE B



NOTES:

- DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION:
- MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER
- SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE –W–.

| | MILLIN | IETERS | INC | HES |
|-----|--------|--------|-------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 6.40 | 6.60 | 0.252 | 0.260 |
| В | 4.30 | 4.50 | 0.169 | 0.177 |
| С | | 1.20 | | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 | BSC | 0.026 | BSC |
| Н | 0.27 | 0.37 | 0.011 | 0.015 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 | BSC | 0.252 | |
| M | ٥° | 80 | ٥° | 80 |

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